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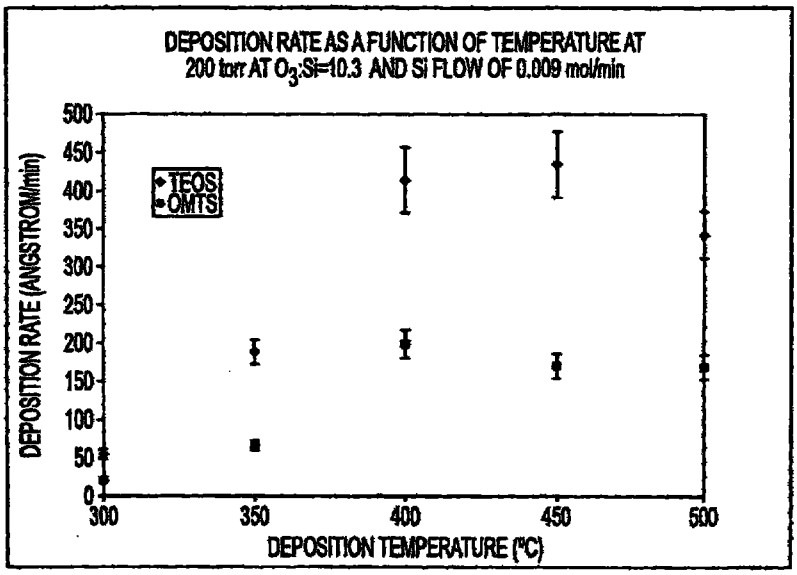
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(54) Title: CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYLSILOXANE OLIGOMERS WITH OZONE




(57) Abstract: A method of depositing an oxide film on the surface of a semiconductor substrate in a chemical vapor deposition system having at least one chamber which comprises providing an alkylsiloxane precursor, providing ozone to said chamber and thermally reacting said alkylsiloxane precursor and ozone to deposit an oxide film on the surface of the substrate.

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